IMFEDK 2013 Awards

■ IEEE EDS Kansai Chapter IMFEDK Best Paper Award

Authors: **Yasufumi Kawai, Shuichi Nagai, Noboru Negoro, Takeshi Fukuda, Tetsuzo Ueda, Nobuyuki Otsuka and Daisuke Ueda** Paper ID: B-2
Title: "A Compact Isolated Gate Driver using GaN HFETs on Sapphire Substrate Integrated with a 5.8GHz Electro-Magnetic Resonant Coupler"
Affiliation: Panasonic Corporation

■ IEEE EDS Kansai Chapter IMFEDK Student Paper Award

Author: **Indra Nur Adisusilo[1]** Paper ID: PA-01
Title: "Monte Carlo Simulation of Seebeck Coefficient of Si Nanostructure with Barrier Layers"
Coauthors: Kentaro Kukita[1] and Yoshinari Kamakura[1,2]
Affiliation: [1]Osaka University, [2]CREST)

Author: **Daiki Sato** Paper ID: PA-02
Title: "Scaling Scheme Prospect of XCT-SOI MOSFET Aiming at MedicalImplant Applications Showing a Long Lifetime with a Small Battery""
Coauthors: Yasuhisa Omura
Affiliation: Kansai University

Author: **Kazuya Mukai[1]** Paper ID: PB-01
Title: "Growth of a sputtered Ta_2O_5/ZnO film and its application to an ion-sensitive field-effect transistor"
Coauthors: Takayuki Onaka[1], Kazuto Koike[1], Toshihiko Maemoto[1], Shigehiko Sasa[1], Mitsuaki Yano[1], Sadao Kadokura[2] and Yutaka Nakamitsu[2]
Affiliation: [1]Osaka Institute of Technology, [2]FTS Corporation)

Author: **Takayuki Kadonome** Paper ID: PC-01
Title: "Retinal Prosthesis of Frequency Modulation using Thin-Film Photo Transistors"
Coauthors: Atsushi Matsumura, Tsuyoshi Higashiyama, Shohei Oyama and Mutsumi Kimura
Affiliation: Ryukoku University

Author: **Satoru Sasaki** Paper ID: PC-02
Title: "Fabrication of zinc oxide transparent thin film transistors on glass substrates by sol-gel method"
Coauthors: Shigehiko Sasa, Ken-Ichi Ogata and Toshihiko Maemoto
Affiliation: Osaka Institute of Technology

Author: **Keisuke Kado[1]** Paper ID: C-4
Title: "Evaluation of TaOx Nanoparticles for Resistive Random Access Memory"
Coauthors: Takahiro Ban[1,2], Mutsunori Uenuma[1,2] and Yasuaki Ishikawa[1,2]
Affiliation: [1]NAIST, [2]CREST

■ **IEEE SSCS Kansai Chapter IMFEDK Student Paper Award**

Author: **Shusuke Yoshimoto[1]** Paper ID: PS-01

Title: "Multiple-Cell-Upset Hardened 6T SRAM Using NMOS-Centered Layout"

Coauthors: Koji Nii[2], Hiroshi Kawaguchi[1] and Masahiko Yoshimoto[1,3]

Affiliation: [1]Kobe University, [2]Renesas Electronics Corporation, [3]JST CREST